

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

Darlington Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CES}	-30	Vdc
Collector - Base Voltage	V _{CBO}	-30	Vdc
Emitter - Base Voltage	V _{EBO}	-10	Vdc
Collector Current – Continuous	Ic	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

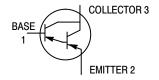


ON Semiconductor®

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SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



2x = Device Code

x = U for MMBTA63LT1G x = V for MMBTA64LT1G

V for MMB1A64L11G SMMBTA64LT1G

M = Date Code*■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA63LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	•
Collector – Emitter Breakdown Voltage (I _C = -100 µAdc)	V _{(BR)CEO}	-30	-	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc)	I _{CBO}	-	-100	nAdc
Emitter Cutoff Current (V _{EB} = -10 Vdc)	I _{EBO}	-	-100	nAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) $ \begin{aligned} &(I_C=-10 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \\ &(I_C=-10 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \\ &(I_C=-100 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \end{aligned} $ $ \begin{aligned} &(I_C=-100 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \end{aligned} $	h _{FE}	5,000 10,000 10,000 20,000	- - -	_
Collector – Emitter Saturation Voltage $(I_C = -100 \text{ mAdc}, I_B = -0.1 \text{ mAdc})$	V _{CE(sat)}	-	-1.5	Vdc
Base – Emitter On Voltage $(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	V _{BE(on)}	-	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				• •
Current – Gain – Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 MHz)	f⊤	125	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

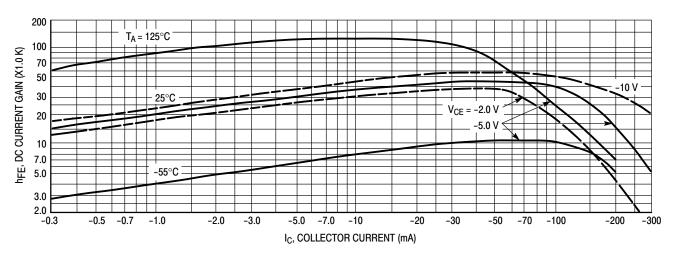


Figure 1. DC Current Gain

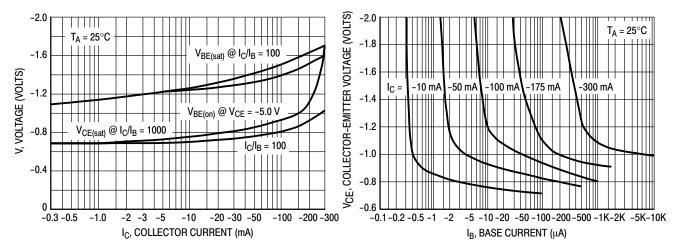


Figure 3. "On" Voltage

1 ms V_{CE} = -5.0 V f = 100 MHz 4.0 ₹ 10 ms _ T_A = 25°C 3.0 IC, COLLECTOR CURRENT 2.0 0.1 100 ms 1 s 1.0 0.01 Thermal Limit 0.4 Single Pulse Test @ $T_A = 25^{\circ}C$ 0.001 -2.0 -20 -50 -100 -200 -500 -1.0 -1K 0.01 1.0 100 IC, COLLECTOR CURRENT (mA) V_{CE}, COLLECTOR-EMITTER VOLTAGE (V)

Figure 4. High Frequency Current Gain

IhFEI, HIGH FREQUENCY CURRENT GAIN

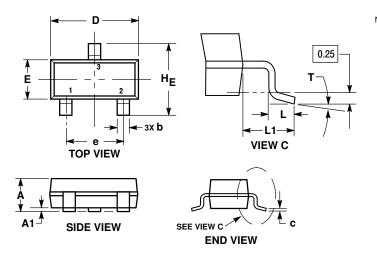
Figure 5. Safe Operating Area

Figure 2. Collector Saturation Region

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- THE BASE MATERIAL.

 DIMENSIONS O AND E DO NOT INCLUDE MOLD FLASH,

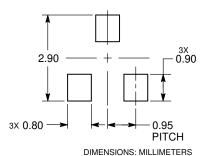
 PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

STYLE 6:

- PIN 1. BASE 2. EMITTER
 - COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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